



**THE DATASHEET OF  
DMTH6010LK3Q-13**



**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
60V	8mΩ @ V <sub>GS</sub> = 10V	70A
	12mΩ @ V <sub>GS</sub> = 4.5V	50A

**Features**

- Rated to 175°C – ideal for high ambient temperature environments
- 100% Unclamped Inductive Switching – ensures more reliable and robust end application
- Low On-Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

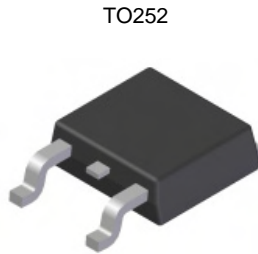
**Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

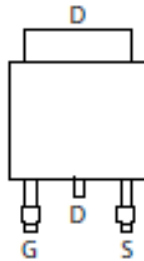
- Engine Management Systems
- Body Control Electronics
- DCDC Converters

**Mechanical Data**

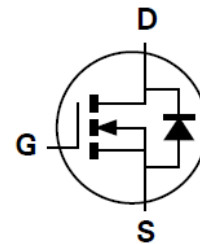
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 Ⓔ3
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



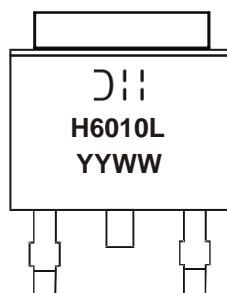
Equivalent Circuit

**Ordering Information** (Note 5)

Part Number	Case	Packaging
DMTH6010LK3Q-13	TO252	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. For more information, please refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



Ⓜ = Manufacturer's Marking  
 H6010L = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 15 = 2015)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	I <sub>D</sub>	T <sub>A</sub> = +25°C	14.8
		T <sub>A</sub> = +70°C	11.9
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 7)	I <sub>D</sub>	T <sub>C</sub> = +25°C	70
		T <sub>C</sub> = +100°C	50
Maximum Continuous Body Diode Forward Current (Note 7)	I <sub>S</sub>	60	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	130	A
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	20	A
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	20	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	31	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	47	°C/W
Total Power Dissipation (Note 7)	P <sub>D</sub>	60	W
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	2.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current (Note 9)	I <sub>DSS</sub>	-	-	1	µA	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V
		-	-	100	µA	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	-	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	6.3	8	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		-	8.3	12		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	-	0.9	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	-	2090	-	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	-	746	-		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	38.5	-		
Gate Resistance	R <sub>g</sub>	0.1	0.59	1.8	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	-	19.3	-	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	-	41.3	-		
Gate-Source Charge	Q <sub>gs</sub>	-	6	-		
Gate-Drain Charge	Q <sub>gd</sub>	-	8.8	-		
Turn-On Delay Time	t <sub>D(ON)</sub>	-	5.7	-	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A, R <sub>g</sub> = 3Ω
Turn-On Rise Time	t <sub>R</sub>	-	4.3	-		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	23.4	-		
Turn-Off Fall Time	t <sub>F</sub>	-	9.7	-		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	35.4	-	ns	I <sub>F</sub> = 20A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	38.2	-	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

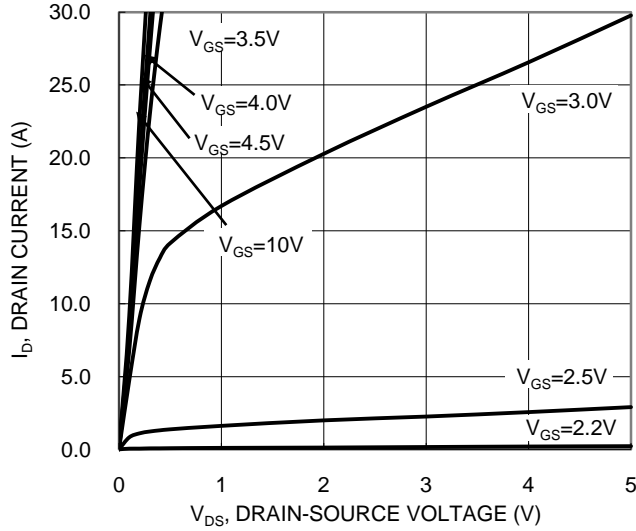


Figure 1. Typical Output Characteristic

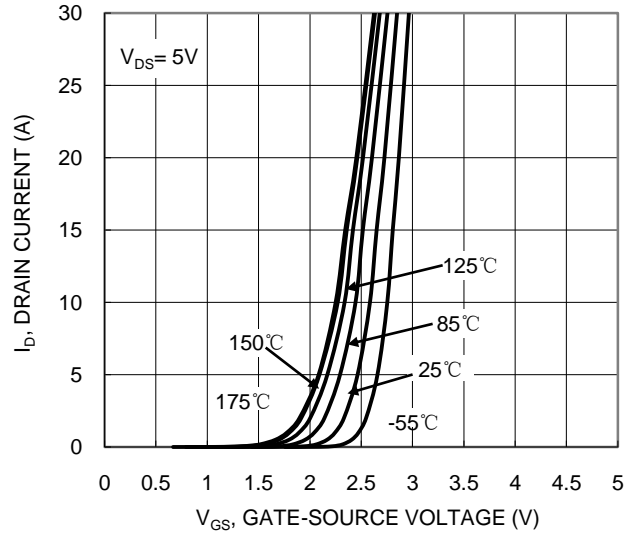


Figure 2. Typical Transfer Characteristic

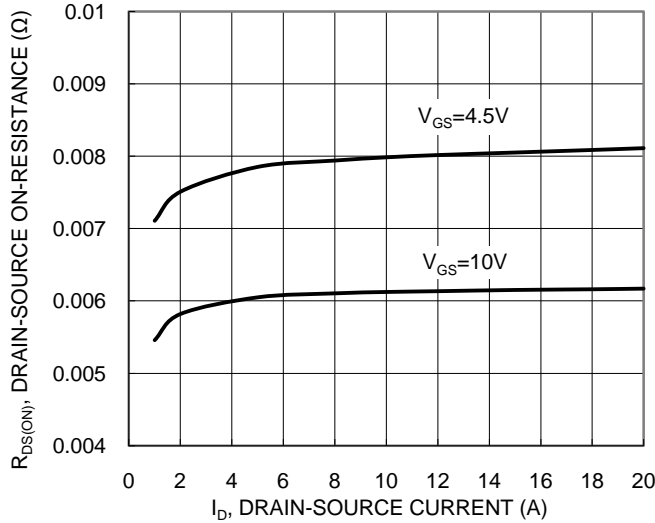


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

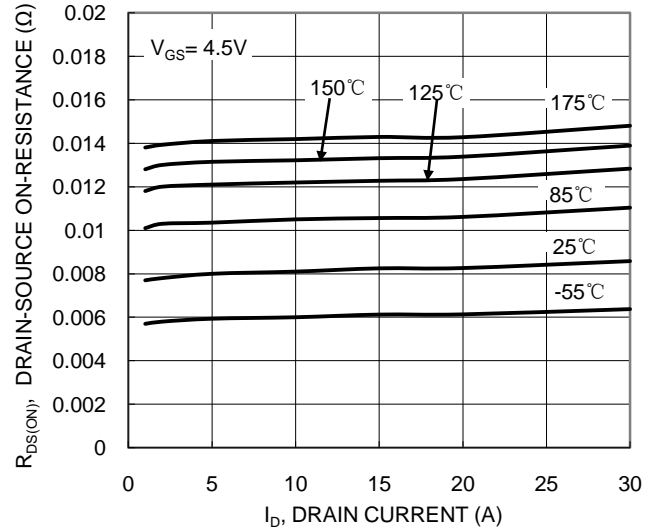


Figure 4. Typical On-Resistance vs. Drain Current and Temperature

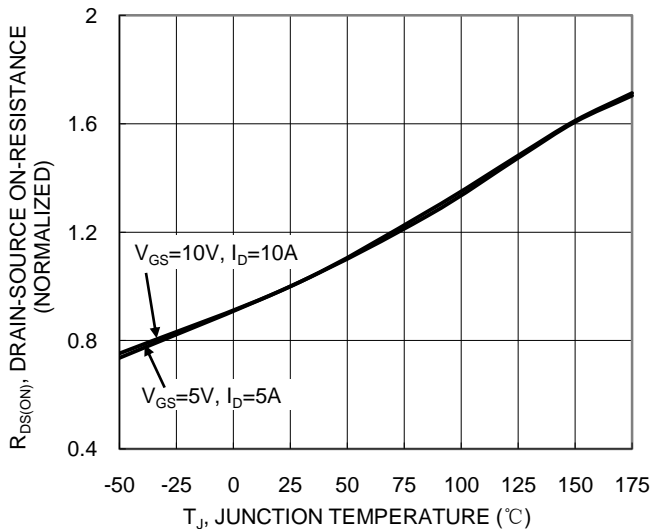


Figure 5. On-Resistance Variation with Temperature

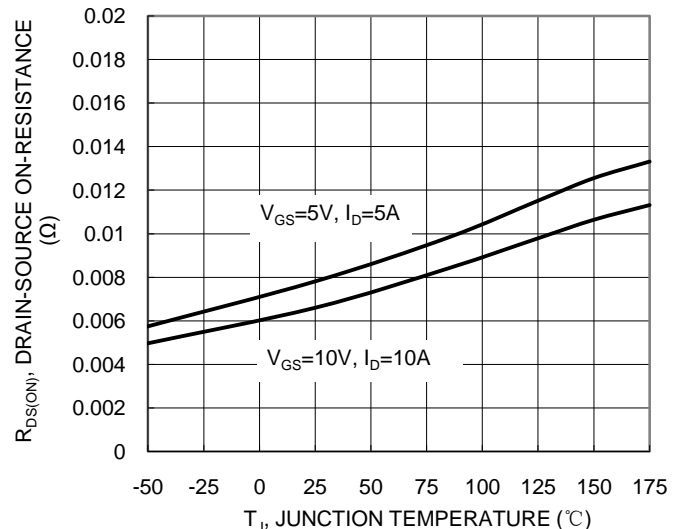


Figure 6. On-Resistance Variation with Temperature

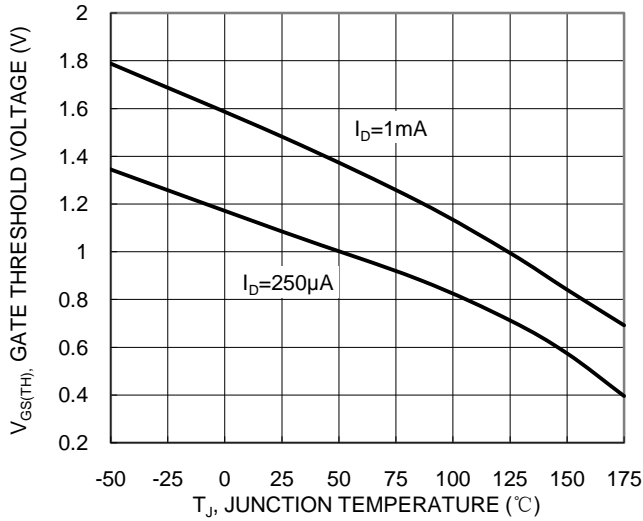


Figure 7. Gate Threshold Variation vs. junction Temperature

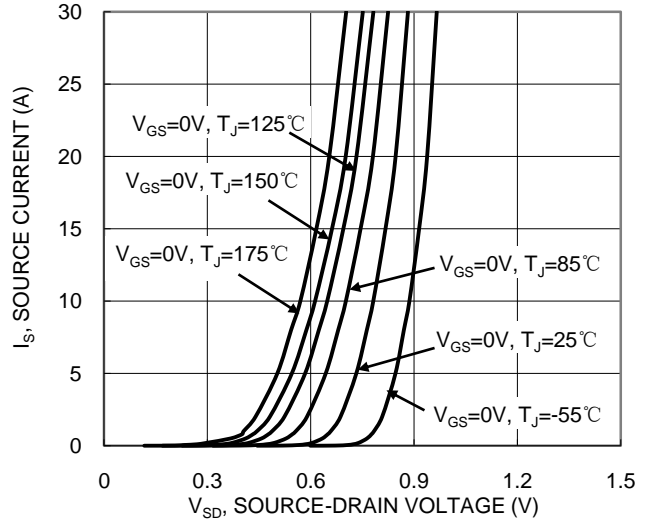


Figure 8. Diode Forward Voltage vs. Current

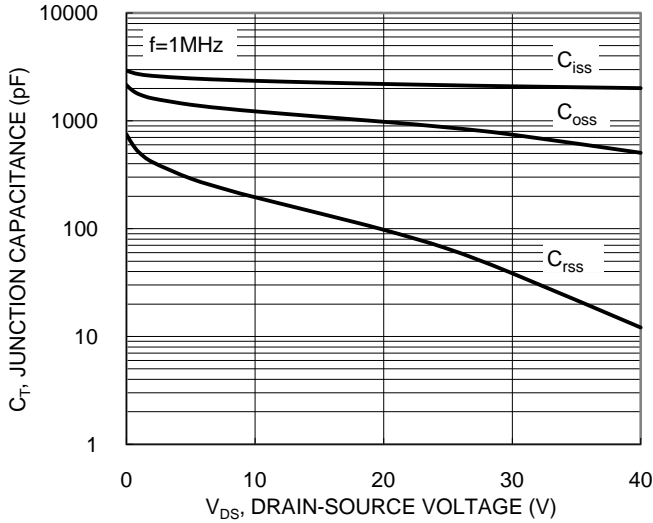


Figure 9. Typical Junction Capacitance

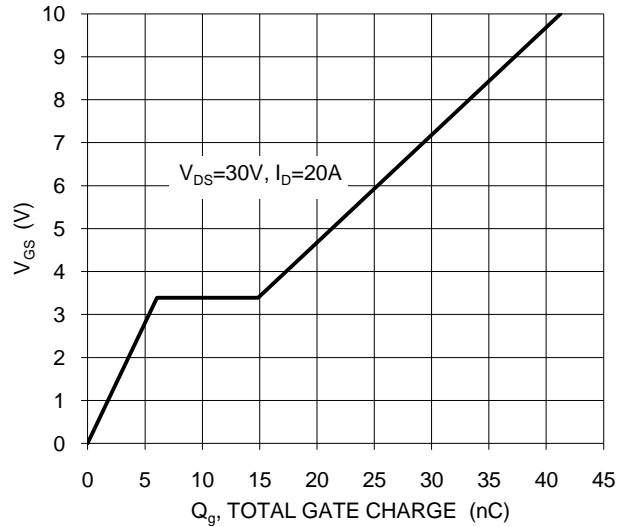


Figure 10. Gate Charge

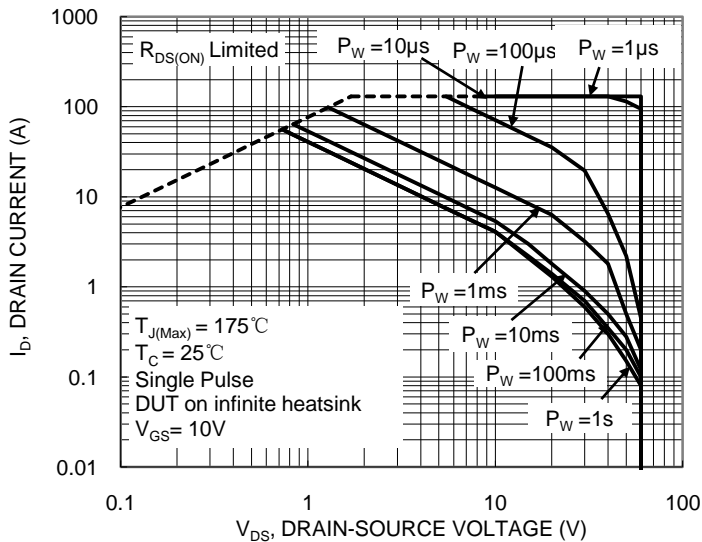


Figure 11. SOA, Safe Operation Area

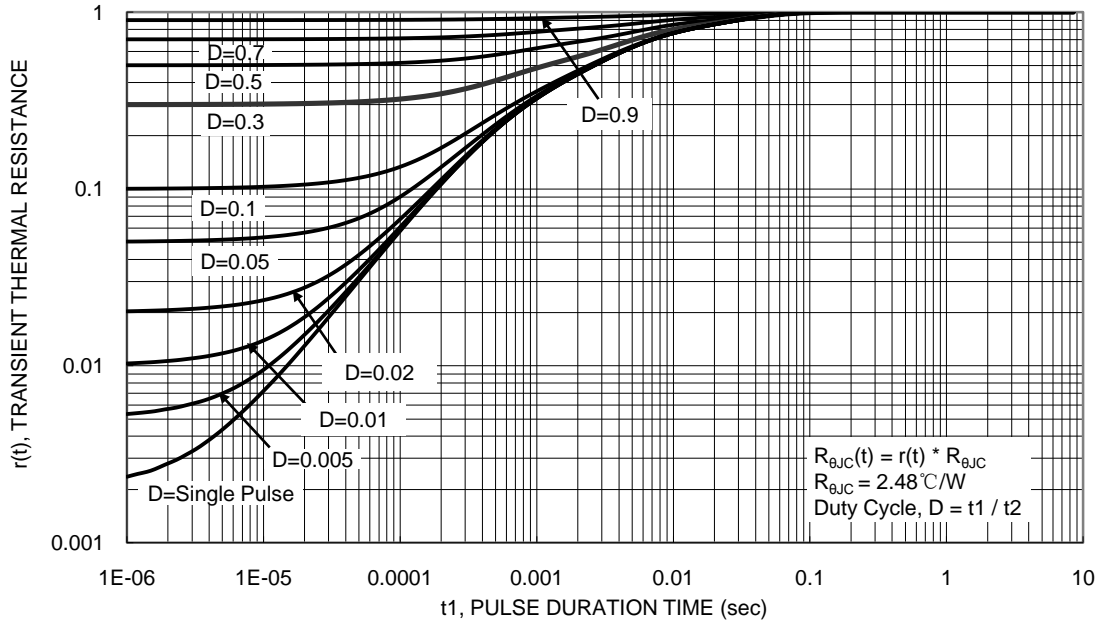
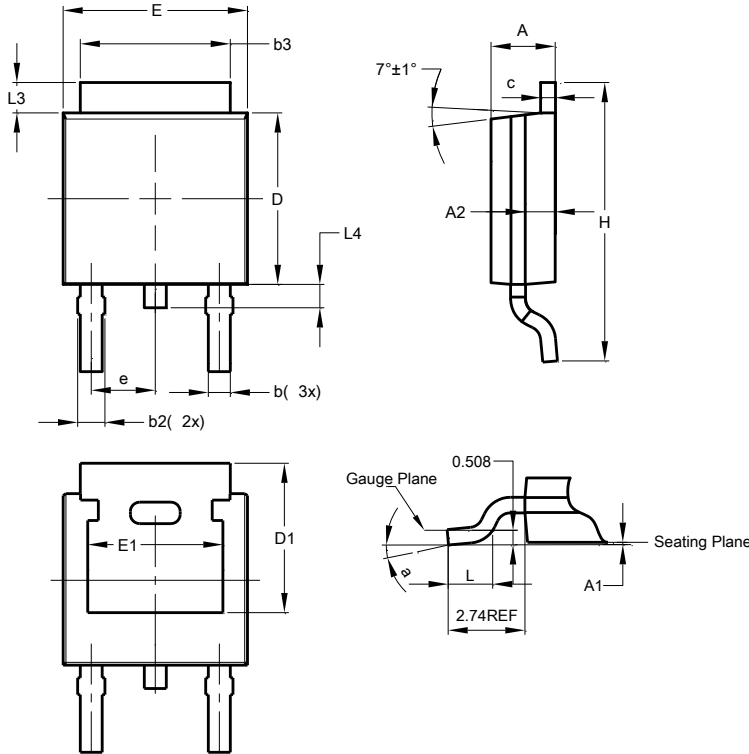


Figure 12 .Transient Thermal Resistance

**Package Outline Dimensions**

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

**TO252 (DPAK)**

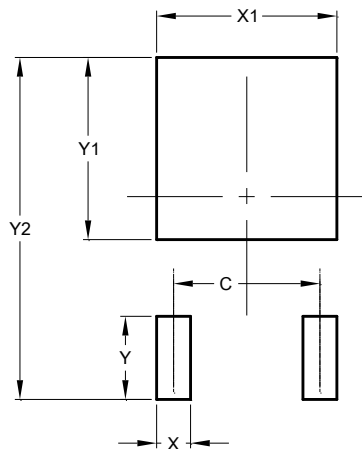


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

**TO252 (DPAK)**



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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